

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (currently amended): A nitride semiconductor substrate comprising:
a group III nitride semiconductor substrate;
a mask formed over the group III nitride semiconductor substrate; and
a group III nitride semiconductor multilayer film formed above the mask,
wherein the group III nitride semiconductor substrate has a dislocation density in a
vicinity of a surface thereof of $1 \times 10^7/\text{cm}^2$ or less,
the mask has a polycrystalline material deposited on a surface thereof,
a part of the mask is not covered with said group III nitride semiconductor multilayer
film, and
voids are formed on the surface of the mask having the polycrystalline material, and
one surface of said polycrystalline material contacts with said mask, and an opposing
surface to said one surface of said polycrystalline material contacts with said semiconductor
multilayer film.

2. (original): The nitride semiconductor substrate according to Claim 1, wherein the
polycrystalline material is formed from a material containing aluminum and nitrogen as essential
elements.

3. (canceled).

4. (original): The nitride semiconductor substrate according to Claim 1, wherein the mask is provided on the surface of the group III nitride semiconductor substrate.

5. (canceled).

6. (currently amended): A nitride semiconductor device comprising:
a group III nitride semiconductor substrate;
a mask formed over the group III nitride semiconductor substrate; and
a group III nitride semiconductor multilayer film formed above the mask, the group III nitride semiconductor multilayer film including an active layer,
wherein the group III nitride semiconductor substrate has a dislocation density in a vicinity of a surface thereof of $1 \times 10^7/\text{cm}^2$ or less,
the mask has a polycrystalline material deposited on a surface thereof,
a part of the mask is not covered with said group III nitride semiconductor multilayer film, and
voids are formed on the surface of the mask having the polycrystalline material, and
one surface of said polycrystalline material contacts with said mask, and an opposing surface to said one surface of said polycrystalline material contacts with said semiconductor multilayer film.

7. (original): The nitride semiconductor device according to Claim 6, wherein the polycrystalline material is formed from a material containing aluminum and nitrogen as essential elements.

8. (canceled).

9. (original): The nitride semiconductor device according to Claim 6, wherein the mask is provided on the surface of the group III nitride semiconductor substrate.

10. (canceled).

11. (previously presented): The nitride semiconductor device according to Claim 6, wherein the mask is provided in a vicinity of a device separating groove of the nitride semiconductor device.

12-25. (canceled).